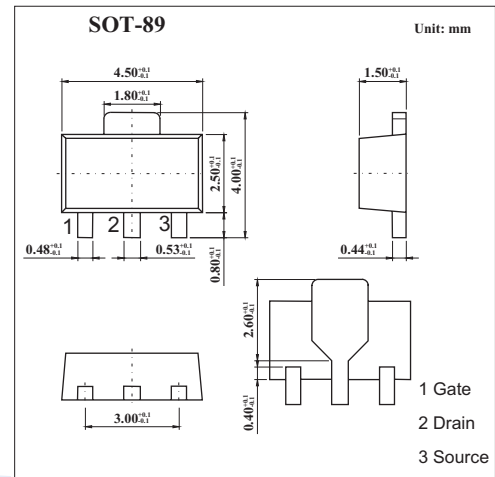
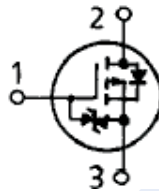


MOS Field Effect Transistors

2SJ360

■ Features

- Low on-state resistance
 $R_{DS(on)} = 0.55 \Omega$ ($V_{GS} = -4V, I_D = -1.0A$)
- High forward transfer admittance : $|Y_{fs}| = 0.9S$ (Typ.)
- Low leakage current : $I_{DSS} = -100 \mu A$ (Max.) ($V_{DS} = -60V$)



■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit
Drain to source voltage	V_{DS}	-60	V
Gate to source voltage	V_{GS}	± 20	V
Drain current (DC)	I_D	-1	A
Drain current(pulse) *	I_D	-3	A
Power dissipation	P_D	0.5	W
Channel temperature	T_{ch}	150	$^\circ C$
Storage temperature	T_{stg}	-55 to +150	$^\circ C$

* $PW \leq 10 \mu s$; $d \leq 1\%$.

2SJ360

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Drain cut-off current	I_{DSS}	$V_{DS}=-60V, V_{GS}=0$			100	μA
Gate leakage current	I_{GSS}	$V_{GS}=\pm 16V, V_{DS}=0$			± 10	μA
Gate threshold voltage	V_{th}	$V_{DS}=-10V, I_D=-1mA$	-0.8		-2.0	V
Forward transfer admittance	$ Y_{fs} $	$V_{DS}=-10V, I_D=-0.5A$	0.5	0.9		S
Drain to source on-state resistance	$R_{DS(on)}$	$V_{GS}=-4V, I_D=-0.5A$		0.86	1.2	Ω
		$V_{GS}=-10V, I_D=-0.5A$		0.55	0.73	Ω
Input capacitance	C_{iss}	$V_{DS}=-10V, V_{GS}=0, f=1MHz$		155		pF
Output capacitance	C_{oss}			20		pF
Reverse transfer capacitance	C_{rss}			75		pF
Turn-on delay time	$t_{d(on)}$	$V_{GS(on)}=-10V, V_{DD}=-30V, I_D=-0.5A$ $R_L=60\Omega$		20		ns
Rise time	t_r			17		ns
Turn-off delay time	$t_{d(off)}$			100		ns
Fall time	t_f			20		ns
Total Gate Charge	Q_g	$V_{GS}=-10V, I_D=-1A, V_{DD}=-48V$		6.5		nC
Gate to Source Charge	Q_{gs}			4.5		nC
Gate Drain Charge	Q_{gd}			2.0		nC
Continuous drain reverse current	I_{DR}				-1	A
Pulse drain reverse current	I_{DRP}				-3	A
Diode forward voltage	V_{DSF}	$I_{DR}=-1A, V_{GS}=0V$			1.7	V
Reverse recovery time	t_{rr}	$I_{DR}=-1A, V_{GS}=0V, di/dt=50A/\mu s$			50	ns
Reverse recovery charge	Q_{rr}				50	μc

■ Marking

Marking	Z8
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